SEP 2 9 2003 &

September 24, 2003

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572 28 Davis Avenue Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/613,694 07/03/03

Yang-Tung Fan et al.

NEW BUMPING PROCESS TO INCREASE BUMP HEIGHT AND TO CREATE A MORE ROBUST BUMP STRUCTURE

Grp. Art Unit:

## INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

## CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on September 16, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

TSMC-00-776B

- U.S. Patent 5,904,156 to Advocate, Jr. et al., "Dry Film Resist Removal in the Presence of Electroplated C4's," discloses a process for a dry film resist removal in the presence of electroplated bumps.
- U.S. Patent 6,211,052 to Farnworth, "Mask Repattern Process," discloses a UBM and bump process using photoresist.
- U.S. Patent 5,914,274 to Yamaguchi et al., "Substrate on which Bumps are Formed and Method of Forming the Same," discloses a substrate on which bumps are formed and a method of forming same.
- U.S. Patent 5,903,058 to Akram, "Conductive Bumps on Die for Flip Chip Application," discloses a process for conductive bumps on a die.

Sincerely

Stephen B. Ackerman,

Reg. No. 37761

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